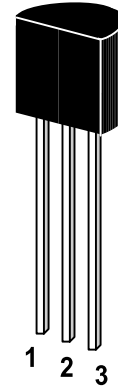


ST 2SD734

NPN Silicon Epitaxial Planar Transistor
for 1W Output, Electronic Governor, DC-DC Converter Applications.

The transistor is subdivided into four groups D, E, F and G, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

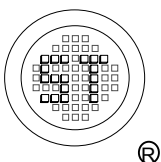


1. Emitter 2. Collector 3. Base

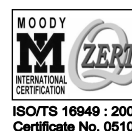
TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	25	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	700	mA
Collector Current (Pulse)	I_{CP}	1500	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$



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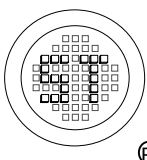
ISO/TS 16949 : 2002 Certificate No. 05103
ISO 14001:2004 Certificate No. 7116
ISO 9001:2000 Certificate No. 0506098

Dated : 07/12/2002

ST 2SD734

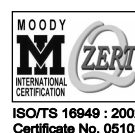
Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit				
DC Current Gain at $V_{CE}=2\text{V}$, $I_C=50\text{mA}$	Current Gain Group	D	h_{FE}	60	-	120	-		
		E	h_{FE}	100	-	200	-		
		F	h_{FE}	160	-	320	-		
		G	h_{FE}	280	-	560	-		
					at $V_{CE}=2\text{V}$, $I_C=500\text{mA}$	h_{FE}	50	-	-
Collector Cutoff Current at $V_{CB}=20\text{V}$	I_{CBO}	-	-	1	μA				
Emitter Cutoff Current at $V_{EB}=4\text{V}$	I_{EBO}	-	-	1	μA				
Gain Bandwidth Product at $V_{CE}=10\text{V}$, $I_C=50\text{mA}$	f_T	-	250	-	MHz				
Output Capacitance at $V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{ob}	-	8	-	pF				



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